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On Feb. 27, 2001

TOWNSEND and TOWNSEND and CREW LLP

By: Andrea J.

PATENT
Attorney Docket No.: A524R1/T28900
TTC No.: 16301-028900

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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In re application of:

KATSUYUKI MUSAKA et al.

Application No.: 09/187,551

Filed: November 5, 1998

For: METHOD FOR FORMING A THIN FILM FOR A SEMICONDUCTOR DEVICE

Examiner: Marianne Padgett

Art Unit: 1762

AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the Office Action mailed October 31, 2000, please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend claims 27 and 33 as follows. Note that the remaining claims are unamended but are reproduced below for the Examiner's convenience and reference.

1. A method of forming a conformal thin film of silicon oxide on a substrate having spaced conductive lines thereon comprising the steps of:

mounting a substrate onto a substrate support in a vacuum chamber;
forming a plasma in the vacuum chamber in a region above the substrate by means of an electrical power source from a reaction gas comprising a mixture of tetraethylorthosilicate and a fluorine-containing halocarbon gas selected from the group

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